

# Silicon Bridge Rectifier

$$V_{RRM} = 50 \text{ V} - 1000 \text{ V}$$

$$I_F = 8 \text{ A}$$

## Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Types up to 1000 V  $V_{RRM}$
- Ideal for printed circuit board
- High surge overload rating
- High temperature soldering guaranteed: 260°C/ 10 seconds, 0.375(9.5mm) lead length
- Glass passivated chip junction
- High case dielectric strength 1500 V<sub>RMS</sub>

## GBU Package



## Mechanical Data

Case: Molded plastic body over passivated junctions

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-750

Method 2026 guaranteed

## Maximum ratings, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                            | Symbol     | Conditions                                        | GBU8J      | GBU8K      | GBU8M      | Unit |
|------------------------------------------------------|------------|---------------------------------------------------|------------|------------|------------|------|
| Repetitive peak reverse voltage                      | $V_{RRM}$  |                                                   | 600        | 800        | 1000       | V    |
| RMS reverse voltage                                  | $V_{RMS}$  |                                                   | 420        | 560        | 700        | V    |
| DC blocking voltage                                  | $V_{DC}$   |                                                   | 600        | 800        | 1000       | V    |
| Continuous forward current                           | $I_F$      | $T_C \leq 100^\circ\text{C}$                      | 8          | 8          | 8          | A    |
| Surge non-repetitive forward current, Half Sine Wave | $I_{F,SM}$ | $T_C = 25^\circ\text{C}$ , $t_p = 8.3 \text{ ms}$ | 200        | 200        | 200        | A    |
| Operating temperature                                | $T_j$      |                                                   | -55 to 150 | -55 to 150 | -55 to 150 | °C   |
| Storage temperature                                  | $T_{stg}$  |                                                   | -55 to 150 | -55 to 150 | -55 to 150 | °C   |

## Electrical characteristics, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter             | Symbol | Conditions                                                                                          | GBU8J    | GBU8K    | GBU8M    | Unit          |
|-----------------------|--------|-----------------------------------------------------------------------------------------------------|----------|----------|----------|---------------|
| Diode forward voltage | $V_F$  | $I_F = 8 \text{ A}$ , $T_j = 25^\circ\text{C}$                                                      | 1.1      | 1.1      | 1.1      | V             |
| Reverse current       | $I_R$  | $V_R = 50 \text{ V}$ , $T_j = 25^\circ\text{C}$<br>$V_R = 50 \text{ V}$ , $T_j = 125^\circ\text{C}$ | 5<br>500 | 5<br>500 | 5<br>500 | $\mu\text{A}$ |

## Thermal characteristics

|                                     |            |  |      |      |      |      |
|-------------------------------------|------------|--|------|------|------|------|
| Thermal resistance, junction - case | $R_{thJA}$ |  | 21.0 | 21.0 | 21.0 | °C/W |
|                                     | $R_{thJL}$ |  | 2.2  | 2.2  | 2.2  |      |

